DOCUMENT CHANGE REQUEST

DCR number	21	Changes required for: N/A	Originator: Ponse
Date: 2003/01/16		Date sent: 2003/01/16	Organisation: DLR
Status: IMPLEMENTED			

Title:	Transistors Microwave Metal Semiconductor Field Effect Power Gallium Arsenide, based on types		
Number:	5614/006	Issue:	1

Other documents affected:

Page:

Paragraph:

Original wording:

Proposed wording:

Justification:

Attachments:

N/A

Modifications:

N/A

Approval signature:

Date signed:

2003-01-16